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| Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET M122-1427 | SERIAL NO. Filed Herewith |
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| **LIST OF ART CITED BY APPLICANT** (Use several sheets if necessary) | APPLICANT Micron Technology, Inc. | |
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APPLICANT
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| APPLICANT Zhiping Yin et al. | |
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| MI22-1427 | 09/557,903 |
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